

Description

The AO3418 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 2.5V. This device is suitable for use as a

Battery protection or in other Switching application.

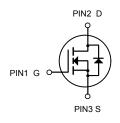


General Features

 $V_{DS} = 30V, I_{D} = 5.8A$

 $R_{DS(ON)} < 28m\Omega$ @ $V_{GS}=10V$

 $R_{DS(ON)} < 38m\Omega$ @ $V_{GS}=4.5V$



N-Channel MOSFET

Application

High power and current handing capability Lead free product is acquired Surface mount package PWM applications Load switch

Power management

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
AO3418	SOT-23-3L	HXY MOSFET	3000

Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	30	V
V _G s	Gate-Source Voltage	±12	V
Ι _D	Drain Current-Continuous	5.8	А
Ідм	Drain Current-Pulsed (Note 1)	20.4	А
PD	Maximum Power Dissipation	1.4	W
T _J ,T _{STG}	Operating Junction and Storage Temperature Range		$^{\circ}$
Reja	Thermal Resistance,Junction-to-Ambient (Note 2)	89	°C/W



Electrical Characteristics (T_J =25 $^{\circ}$ C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250μA	30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =30V, V _{GS} =0V,	-	-	1.0	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±12V	_	-	±100	nA
V _{GS(th)}	Gate Threshold Voltage	$V_{DS}=V_{GS}$, $I_D=250\mu A$	0.5	-	1.3	V
	Static Drain-Source on-Resistance	V _{GS} =10V, I _D =4A	-	24	28	mΩ
$R_{DS(on)}$		V _{GS} =4.5V, I _D =3A	-	27	38	
		V _{GS} =2.5V, I _D =3A	-	36	54	
C _{iss}	Input Capacitance	., .=.,,,	-	507	-	pF
Coss	Output Capacitance	V _{DS} =15V, V _{GS} =0V,	-	52	-	pF
Crss	Reverse Transfer Capacitance	f=1.0MHz	-	43	-	pF
Qg	Total Gate Charge	., ,=,,, =,	-	9.1	-	nC
Q _{gs}	Gate-Source Charge V _{DS} =15V, I _D =5A,		-	2.1	-	nC
Q_{gd}	Gate-Drain("Miller") Charge	V _{GS} =4.5V	-	2.8	-	nC
t _{d(on)}	Turn-on Delay Time		_	3	-	ns
t _r	Turn-on Rise Time	V_{DS} =15V, R_{GEN} =3 Ω ,	-	2.8	-	ns
t _{d(off)}	Turn-off Delay Time	R _L =2.8Ω, V _{GS} =10V	-	25	-	ns
t _f	Turn-off Fall Time		-	4	-	ns
Is	Maximum Continuous Drain to Source Diode Forward Current		-	-	5	А
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	20	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} =0V, I _S =5A	-	-	1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

^{2.} Pulse Test: Pulse Width≤300µs, Duty Cycle≤0.5%



Typical Performance Characteristics

Figure1: Output Characteristics

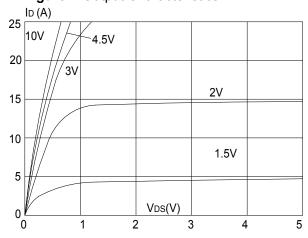


Figure 2: Typical Transfer Characteristics

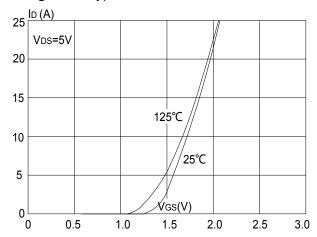


Figure 3:On-resistance vs. Drain Current Ros(on) (m Ω)

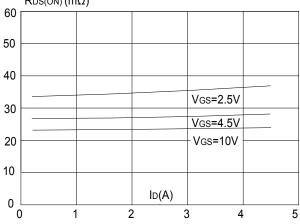


Figure 4: Body Diode Characteristics

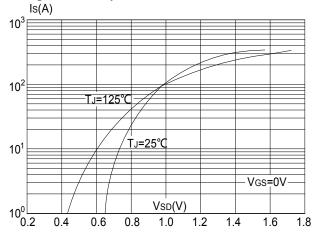


Figure 5: Gate Charge Characteristics

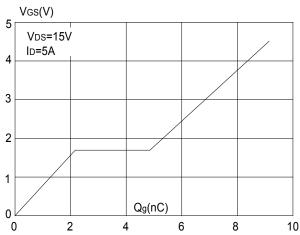
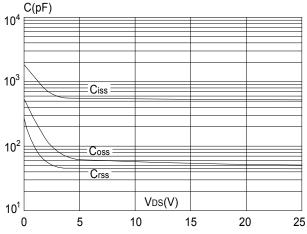


Figure 6: Capacitance Characteristics



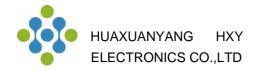


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

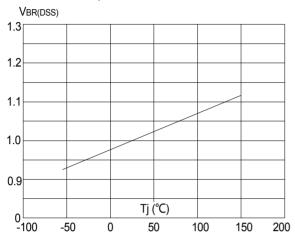


Figure 9: Maximum Safe Operating Area

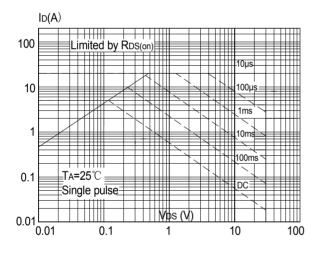


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

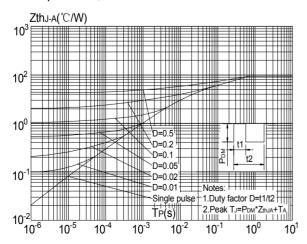


Figure 8: Normalized on Resistance vs. Junction Temperature

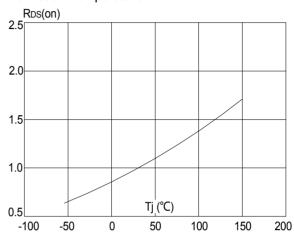
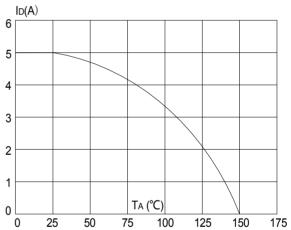
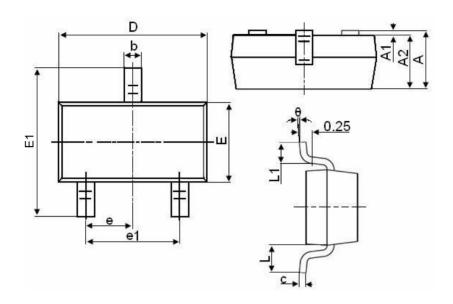


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature





SOT-23-3LPackage Information



Symbol	Dimensions in Millimeters		
	MIN.	MAX.	
А	1.050	1.250	
A1	0.000	0.100	
A2	1.050	1.150	
b	0.300	0.500	
С	0.100	0.200	
D	2.800	3.000	
E	1.500	1.700	
E1	2.650	2.950	
е		0.950TYP	
e1	1.800	2.000	
L	0.550REF		
L1	0.300	0.600	
θ	0°	8°	



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